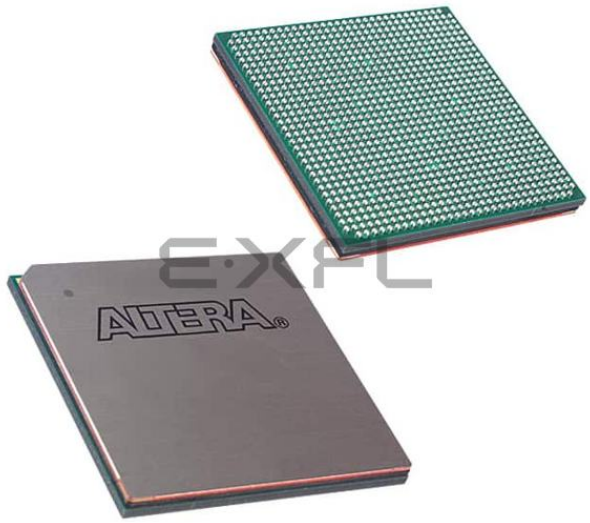

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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	2566
Number of Logic Elements/Cells	25660
Total RAM Bits	1944576
Number of I/O	706
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	1020-BBGA
Supplier Device Package	1020-FBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1s25f1020c6

2. Stratix Architecture

S51002-3.2

Functional Description

Stratix® devices contain a two-dimensional row- and column-based architecture to implement custom logic. A series of column and row interconnects of varying length and speed provide signal interconnects between logic array blocks (LABs), memory block structures, and DSP blocks.

The logic array consists of LABs, with 10 logic elements (LEs) in each LAB. An LE is a small unit of logic providing efficient implementation of user logic functions. LABs are grouped into rows and columns across the device.

M512 RAM blocks are simple dual-port memory blocks with 512 bits plus parity (576 bits). These blocks provide dedicated simple dual-port or single-port memory up to 18-bits wide at up to 318 MHz. M512 blocks are grouped into columns across the device in between certain LABs.

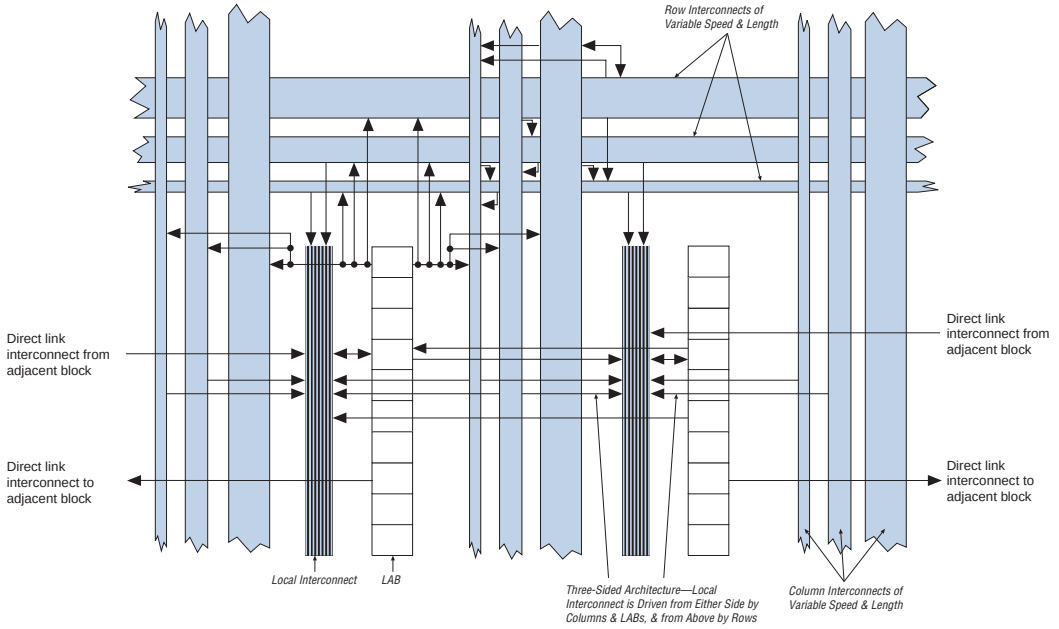
M4K RAM blocks are true dual-port memory blocks with 4K bits plus parity (4,608 bits). These blocks provide dedicated true dual-port, simple dual-port, or single-port memory up to 36-bits wide at up to 291 MHz. These blocks are grouped into columns across the device in between certain LABs.

M-RAM blocks are true dual-port memory blocks with 512K bits plus parity (589,824 bits). These blocks provide dedicated true dual-port, simple dual-port, or single-port memory up to 144-bits wide at up to 269 MHz. Several M-RAM blocks are located individually or in pairs within the device's logic array.

Digital signal processing (DSP) blocks can implement up to either eight full-precision 9 × 9-bit multipliers, four full-precision 18 × 18-bit multipliers, or one full-precision 36 × 36-bit multiplier with add or subtract features. These blocks also contain 18-bit input shift registers for digital signal processing applications, including FIR and infinite impulse response (IIR) filters. DSP blocks are grouped into two columns in each device.

Each Stratix device I/O pin is fed by an I/O element (IOE) located at the end of LAB rows and columns around the periphery of the device. I/O pins support numerous single-ended and differential I/O standards. Each IOE contains a bidirectional I/O buffer and six registers for registering input, output, and output-enable signals. When used with

Figure 2–2. Stratix LAB Structure



LAB Interconnects

The LAB local interconnect can drive LEs within the same LAB. The LAB local interconnect is driven by column and row interconnects and LE outputs within the same LAB. Neighboring LABs, M512 RAM blocks, M4K RAM blocks, or DSP blocks from the left and right can also drive an LAB's local interconnect through the direct link connection. The direct link connection feature minimizes the use of row and column interconnects, providing higher performance and flexibility. Each LE can drive 30 other LEs through fast local and direct link interconnects. Figure 2–3 shows the direct link connection.

can drive other R8 interconnects to extend their range as well as C8 interconnects for row-to-row connections. One R8 interconnect is faster than two R4 interconnects connected together.

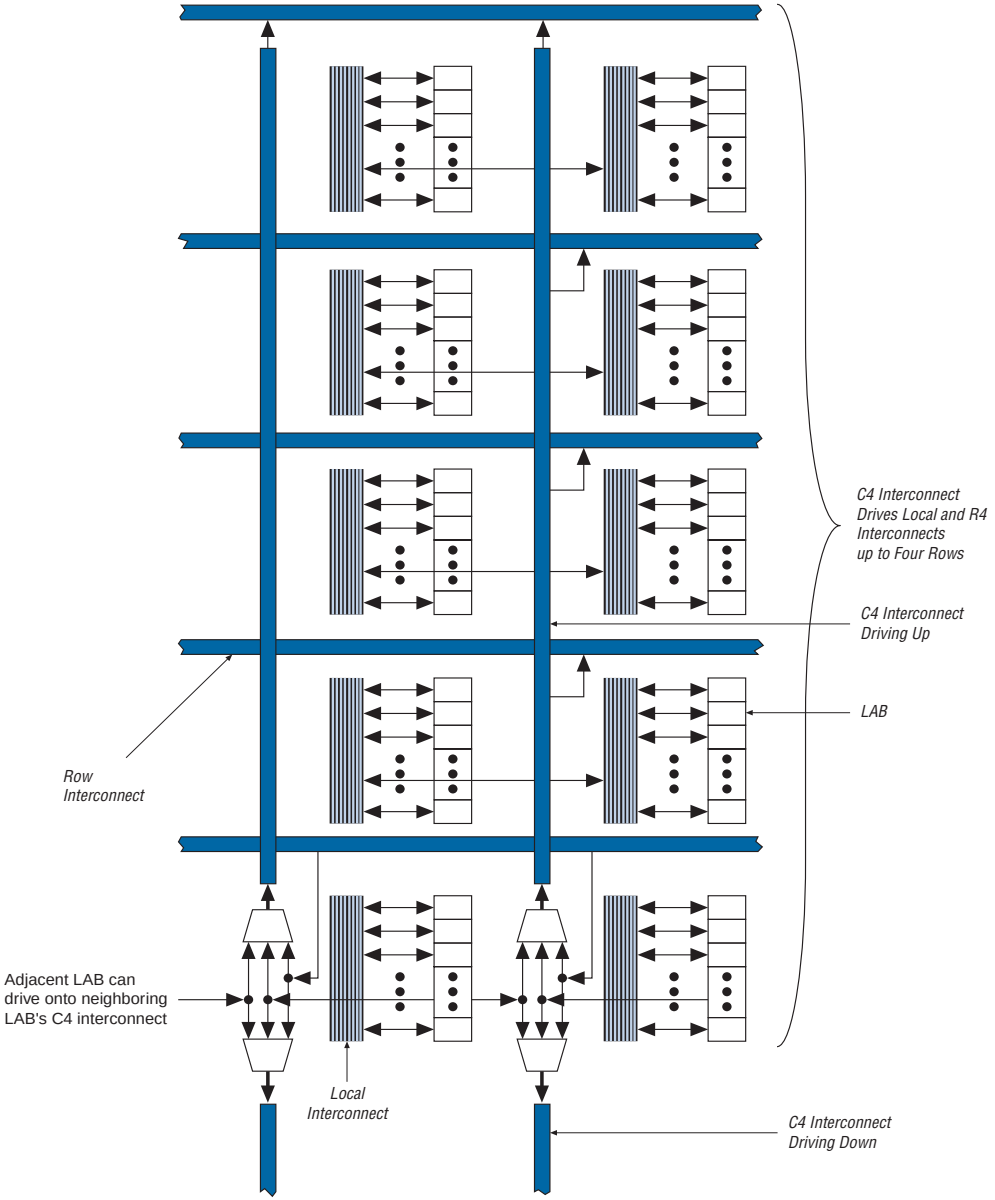
R24 row interconnects span 24 LABs and provide the fastest resource for long row connections between LABs, TriMatrix memory, DSP blocks, and IOEs. The R24 row interconnects can cross M-RAM blocks. R24 row interconnects drive to other row or column interconnects at every fourth LAB and do not drive directly to LAB local interconnects. R24 row interconnects drive LAB local interconnects via R4 and C4 interconnects. R24 interconnects can drive R24, R4, C16, and C4 interconnects.

The column interconnect operates similarly to the row interconnect and vertically routes signals to and from LABs, TriMatrix memory, DSP blocks, and IOEs. Each column of LABs is served by a dedicated column interconnect, which vertically routes signals to and from LABs, TriMatrix memory and DSP blocks, and horizontal IOEs. These column resources include:

- LUT chain interconnects within an LAB
- Register chain interconnects within an LAB
- C4 interconnects traversing a distance of four blocks in up and down direction
- C8 interconnects traversing a distance of eight blocks in up and down direction
- C16 column interconnects for high-speed vertical routing through the device

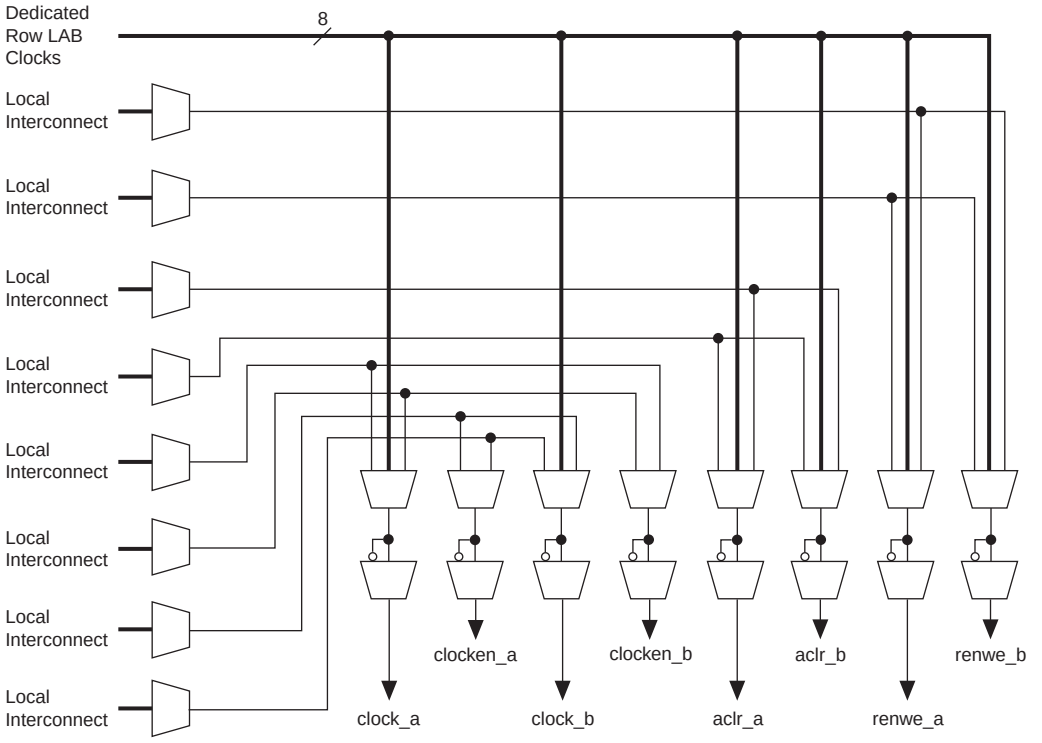
Stratix devices include an enhanced interconnect structure within LABs for routing LE output to LE input connections faster using LUT chain connections and register chain connections. The LUT chain connection allows the combinatorial output of an LE to directly drive the fast input of the LE right below it, bypassing the local interconnect. These resources can be used as a high-speed connection for wide fan-in functions from LE 1 to LE 10 in the same LAB. The register chain connection allows the register output of one LE to connect directly to the register input of the next LE in the LAB for fast shift registers. The Quartus II Compiler automatically takes advantage of these resources to improve utilization and performance. Figure 2–10 shows the LUT chain and register chain interconnects.

Figure 2–11. C4 Interconnect Connections Note (1)



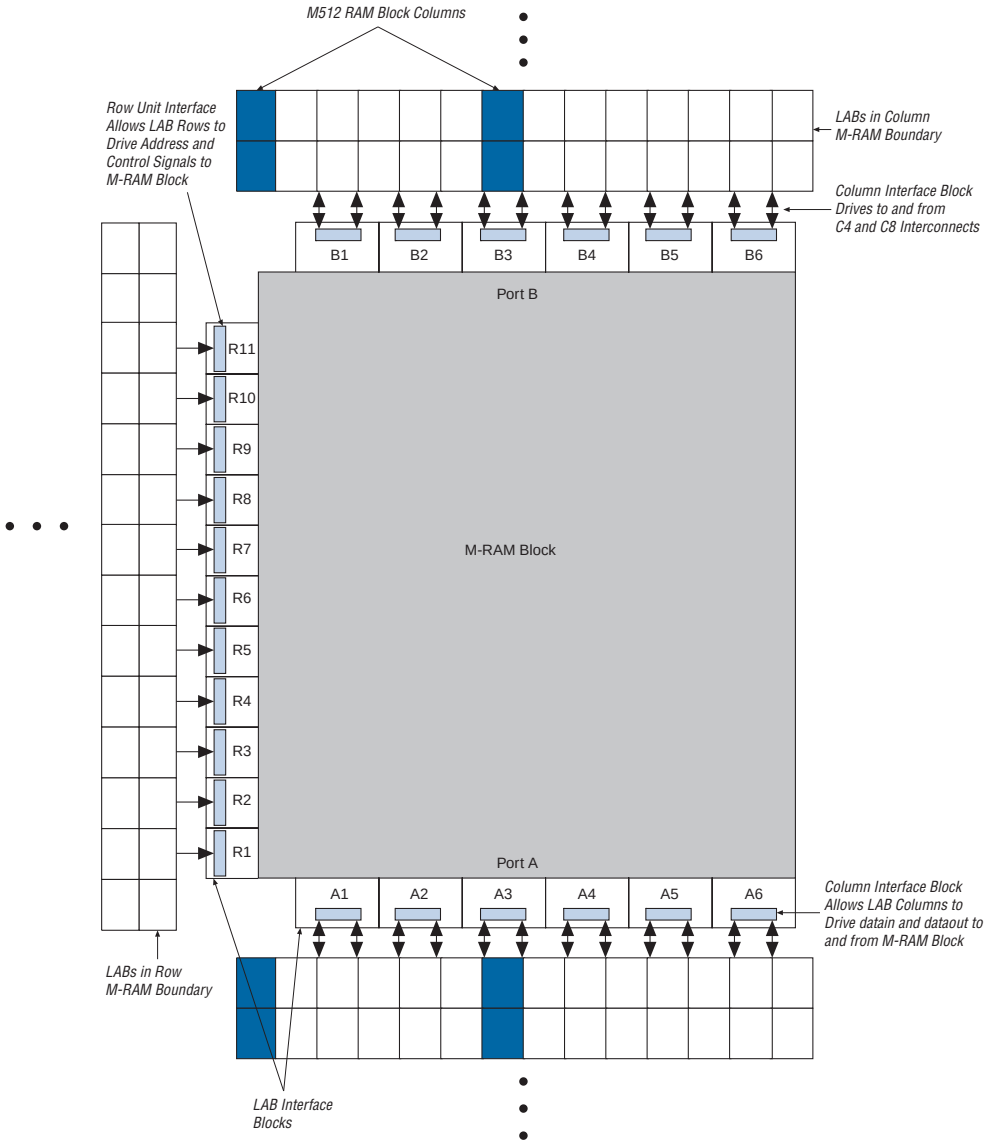
Note to Figure 2–11:
(1) Each C4 interconnect can drive either up or down four rows.

Figure 2–19. M-RAM Block Control Signals



One of the M-RAM block's horizontal sides drive the address and control signal (clock, renwe, byteena, etc.) inputs. Typically, the horizontal side closest to the device perimeter contains the interfaces. The one exception is when two M-RAM blocks are paired next to each other. In this case, the side of the M-RAM block opposite the common side of the two blocks contains the input interface. The top and bottom sides of any M-RAM block contain data input and output interfaces to the logic array. The top side has 72 data inputs and 72 data outputs for port B, and the bottom side has another 72 data inputs and 72 data outputs for port A. Figure 2–20 shows an example floorplan for the EP1S60 device and the location of the M-RAM interfaces.

Figure 2–21. Left-Facing M-RAM to Interconnect Interface Notes (1), (2)



Notes to Figure 2–21:

(1) Only R24 and C16 interconnects cross the M-RAM block boundaries.

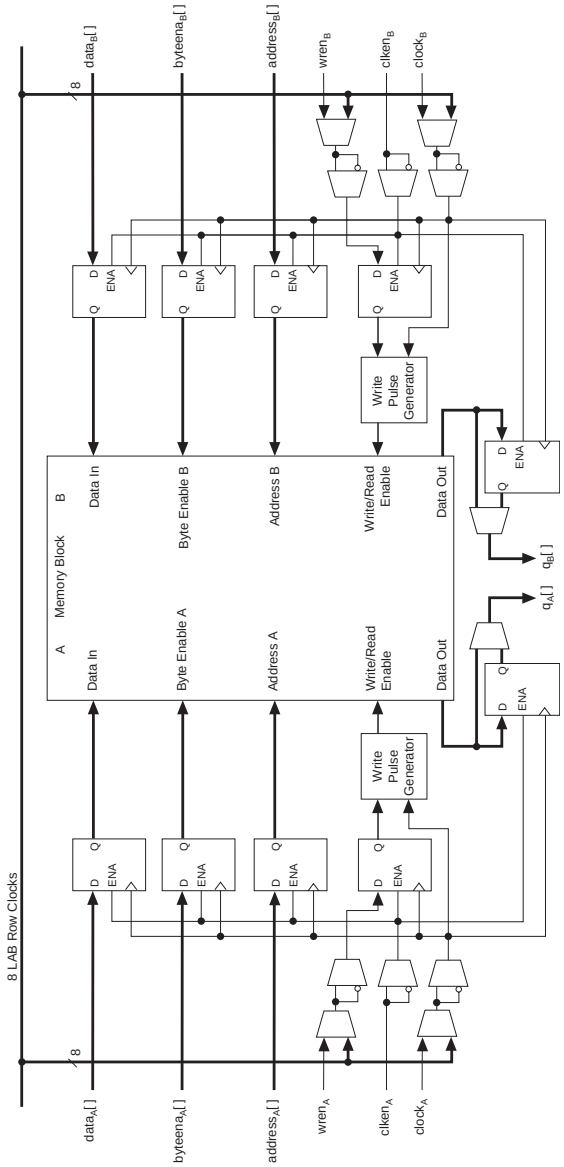
(2) The right-facing M-RAM block has interface blocks on the right side, but none on the left. B1 to B6 and A1 to A6 orientation is clipped across the vertical axis for right-facing M-RAM blocks.

Table 2–12 shows the input and output data signal connections for the column units (B1 to B6 and A1 to A6). It also shows the address and control signal input connections to the row units (R1 to R11).

Table 2–12. M-RAM Row & Column Interface Unit Signals

Unit Interface Block	Input SIgnals	Output Signals
R1	addressa[7..0]	
R2	addressa[15..8]	
R3	byte_enable_a[7..0] renwe_a	
R4	-	
R5	-	
R6	clock_a clocken_a clock_b clocken_b	
R7	-	
R8	-	
R9	byte_enable_b[7..0] renwe_b	
R10	addressb[15..8]	
R11	addressb[7..0]	
B1	datain_b[71..60]	dataout_b[71..60]
B2	datain_b[59..48]	dataout_b[59..48]
B3	datain_b[47..36]	dataout_b[47..36]
B4	datain_b[35..24]	dataout_b[35..24]
B5	datain_b[23..12]	dataout_b[23..12]
B6	datain_b[11..0]	dataout_b[11..0]
A1	datain_a[71..60]	dataout_a[71..60]
A2	datain_a[59..48]	dataout_a[59..48]
A3	datain_a[47..36]	dataout_a[47..36]
A4	datain_a[35..24]	dataout_a[35..24]
A5	datain_a[23..12]	dataout_a[23..12]
A6	datain_a[11..0]	dataout_a[11..0]

Figure 2–24. Independent Clock Mode Notes (1), (2)



Notes to Figure 2–24

(1) All registers shown have asynchronous clear ports.

(2) Violating the setup or hold time on the address registers could corrupt the memory contents. This applies to both read and write operations.

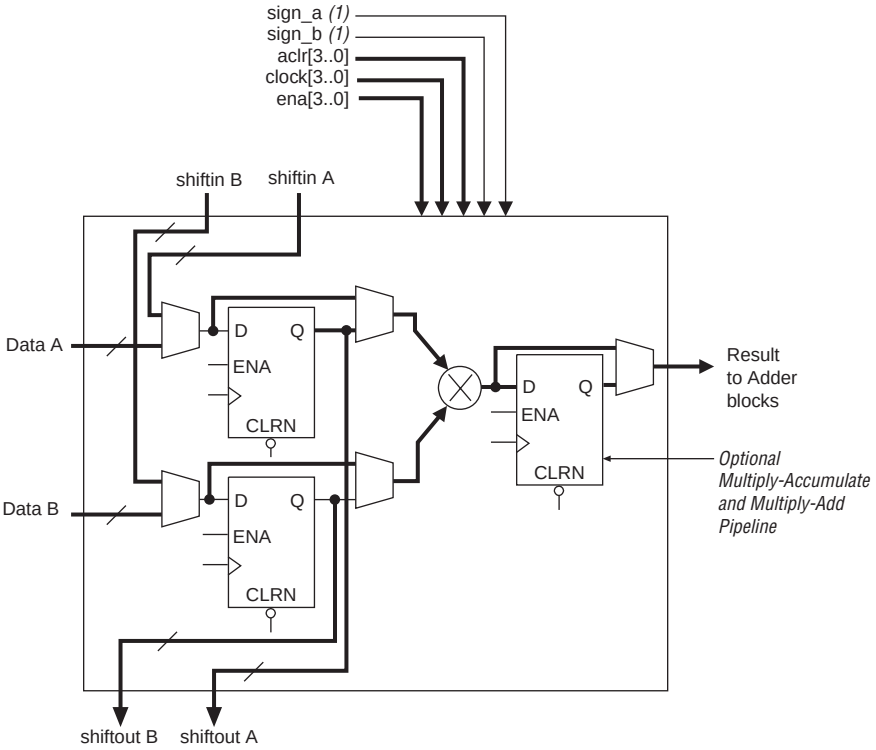
The DSP block consists of the following elements:

- Multiplier block
- Adder/output block

Multiplier Block

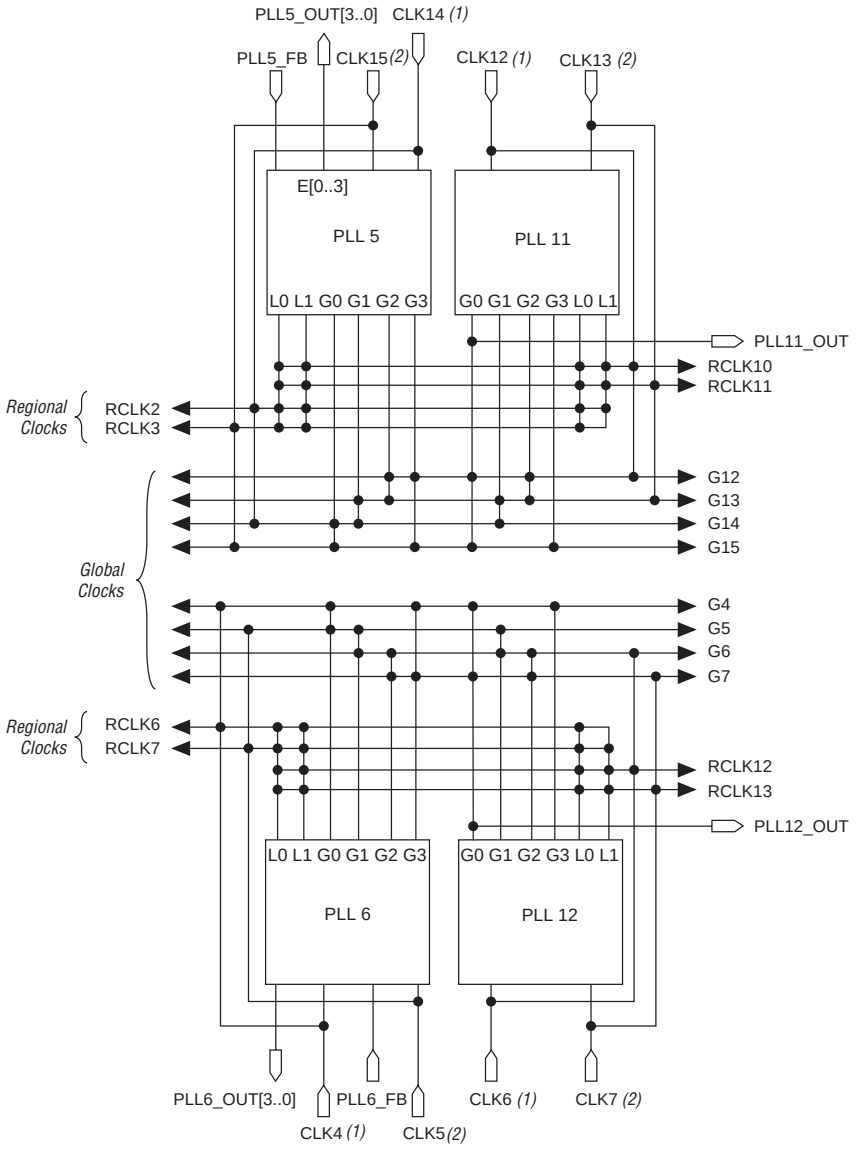
The DSP block multiplier block consists of the input registers, a multiplier, and pipeline register for pipelining multiply-accumulate and multiply-add/subtract functions as shown in Figure 2–32.

Figure 2–32. Multiplier Sub-Block within Stratix DSP Block



Note to Figure 2–32:
(1) These signals can be unregistered or registered once to match data path pipelines if required.

Figure 2–51. Global & Regional Clock Connections from Top Clock Pins & Enhanced PLL Outputs Note (1)



Notes to Figure 2–51:

(1) PLLs 1 to 4 and 7 to 10 are fast PLLs. PLLs 5, 6, 11, and 12 are enhanced PLLs.
(2) `CLK4`, `CLK6`, `CLK12`, and `CLK14` feed the corresponding PLL's `inclk0` port.
(3) `CLK5`, `CLK7`, `CLK13`, and `CLK15` feed the corresponding PLL's `inclk1` port.
(4) The EP1S40 device in the 780-pin FineLine BGA package does not support PLLs 11 and 12.

Table 2–27. DQS & DQ Bus Mode Support (Part 2 of 2) Note (1)

Device	Package	Number of ×8 Groups	Number of ×16 Groups	Number of ×32 Groups
EP1S25	672-pin BGA 672-pin FineLine BGA	16 (3)	8	4
	780-pin FineLine BGA 1,020-pin FineLine BGA	20	8	4
EP1S30	956-pin BGA 780-pin FineLine BGA 1,020-pin FineLine BGA	20	8	4
EP1S40	956-pin BGA 1,020-pin FineLine BGA 1,508-pin FineLine BGA	20	8	4
EP1S60	956-pin BGA 1,020-pin FineLine BGA 1,508-pin FineLine BGA	20	8	4
EP1S80	956-pin BGA 1,508-pin FineLine BGA 1,923-pin FineLine BGA	20	8	4

Notes to Table 2–27:

(1) See the *Selectable I/O Standards in Stratix & Stratix GX Devices* chapter in the *Stratix Device Handbook, Volume 2* for V_{REF} guidelines.
(2) These packages have six groups in I/O banks 3 and 4 and six groups in I/O banks 7 and 8.
(3) These packages have eight groups in I/O banks 3 and 4 and eight groups in I/O banks 7 and 8.
(4) This package has nine groups in I/O banks 3 and 4 and nine groups in I/O banks 7 and 8.
(5) These packages have three groups in I/O banks 3 and 4 and four groups in I/O banks 7 and 8.

A compensated delay element on each DQS pin automatically aligns input DQS synchronization signals with the data window of their corresponding DQ data signals. The DQS signals drive a local DQS bus in the top and bottom I/O banks. This DQS bus is an additional resource to the I/O clocks and is used to clock DQ input registers with the DQS signal.

Two separate single phase-shifting reference circuits are located on the top and bottom of the Stratix device. Each circuit is driven by a system reference clock through the `CLK` pins that is the same frequency as the DQS signal. Clock pins `CLK[15..12]p` feed the phase-shift circuitry on the top of the device and clock pins `CLK[7..4]p` feed the phase-shift circuitry on the bottom of the device. The phase-shifting reference circuit on the top of the device controls the compensated delay elements for all 10 DQS pins located at the top of the device. The phase-shifting reference circuit on the bottom of the device controls the compensated delay elements for all 10 DQS pins located on the bottom of the device. All 10 delay elements (DQS signals) on either the top or bottom of the device

Table 4–20. SSTL-2 Class I Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{CCIO}	Output supply voltage		2.375	2.5	2.625	V
V_{TT}	Termination voltage		V_{REF} – 0.04	V_{REF}	V_{REF} + 0.04	V
V_{REF}	Reference voltage		1.15	1.25	1.35	V
$V_{IH(DC)}$	High-level DC input voltage		V_{REF} + 0.18		3.0	V
$V_{IL(DC)}$	Low-level DC input voltage		–0.3		V_{REF} – 0.18	V
$V_{IH(AC)}$	High-level AC input voltage		V_{REF} + 0.35			V
$V_{IL(AC)}$	Low-level AC input voltage				V_{REF} – 0.35	V
V_{OH}	High-level output voltage	I_{OH} = –8.1 mA *(3)*	V_{TT} + 0.57			V
V_{OL}	Low-level output voltage	I_{OL} = 8.1 mA *(3)*			V_{TT} – 0.57	V

Table 4–21. SSTL-2 Class II Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{CCIO}	Output supply voltage		2.375	2.5	2.625	V
V_{TT}	Termination voltage		V_{REF} – 0.04	V_{REF}	V_{REF} + 0.04	V
V_{REF}	Reference voltage		1.15	1.25	1.35	V
$V_{IH(DC)}$	High-level DC input voltage		V_{REF} + 0.18		V_{CCIO} + 0.3	V
$V_{IL(DC)}$	Low-level DC input voltage		–0.3		V_{REF} – 0.18	V
$V_{IH(AC)}$	High-level AC input voltage		V_{REF} + 0.35			V
$V_{IL(AC)}$	Low-level AC input voltage				V_{REF} – 0.35	V
V_{OH}	High-level output voltage	I_{OH} = –16.4 mA *(3)*	V_{TT} + 0.76			V
V_{OL}	Low-level output voltage	I_{OL} = 16.4 mA *(3)*			V_{TT} – 0.76	V

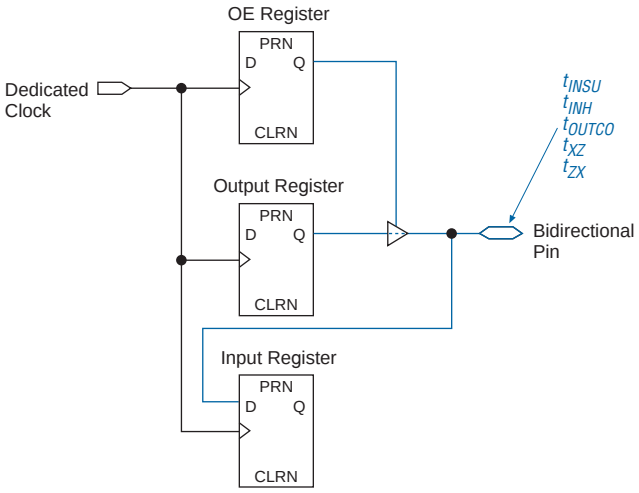
Table 4–22. SSTL-3 Class I Specifications (Part 1 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{CCIO}	Output supply voltage		3.0	3.3	3.6	V
V_{TT}	Termination voltage		V_{REF} – 0.05	V_{REF}	V_{REF} + 0.05	V
V_{REF}	Reference voltage		1.3	1.5	1.7	V
$V_{IH(DC)}$	High-level DC input voltage		V_{REF} + 0.2		V_{CCIO} + 0.3	V
$V_{IL(DC)}$	Low-level DC input voltage		–0.3		V_{REF} – 0.2	V
$V_{IH(AC)}$	High-level AC input voltage		V_{REF} + 0.4			V

External Timing Parameters

External timing parameters are specified by device density and speed grade. Figure 4–4 shows the pin-to-pin timing model for bidirectional IOE pin timing. All registers are within the IOE.

Figure 4–4. External Timing in Stratix Devices



All external timing parameters reported in this section are defined with respect to the dedicated clock pin as the starting point. All external I/O timing parameters shown are for 3.3-V LVTTL I/O standard with the 24-mA current strength and fast slew rate. For external I/O timing using standards other than LVTTL or for different current strengths, use the I/O standard input and output delay adders in Tables 4–103 through 4–108.

Table 4–69. EP1S25 External I/O Timing on Column Pins Using Global Clock Networks

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.371		1.471		1.657		1.916		ns
t_{INH}	0.000		0.000		0.000		0.000		ns
t_{OUTCO}	2.809	5.516	2.809	5.890	2.809	6.429	2.809	7.155	ns
t_{XZ}	2.749	5.390	2.749	5.758	2.749	6.305	2.749	7.040	ns
t_{ZX}	2.749	5.390	2.749	5.758	2.749	6.305	2.749	7.040	ns
$t_{INSUPLL}$	1.271		1.327		1.491		1.677		ns
t_{INHPLL}	0.000		0.000		0.000		0.000		ns
$t_{OUTCOPLL}$	1.124	2.396	1.124	2.492	1.124	2.522	1.124	2.602	ns
t_{XZPLL}	1.064	2.270	1.064	2.360	1.064	2.398	1.064	2.487	ns
t_{ZXPLL}	1.064	2.270	1.064	2.360	1.064	2.398	1.064	2.487	ns

Table 4–70. EP1S25 External I/O Timing on Row Pins Using Fast Regional Clock Networks

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.429		2.631		2.990		3.503		ns
t_{INH}	0.000		0.000		0.000		0.000		ns
t_{OUTCO}	2.376	4.821	2.376	5.131	2.376	5.538	2.376	6.063	ns
t_{XZ}	2.403	4.875	2.403	5.187	2.403	5.606	2.403	6.145	ns
t_{ZX}	2.403	4.875	2.403	5.187	2.403	5.606	2.403	6.145	ns

Table 4–75. EP1S30 External I/O Timing on Column Pins Using Global Clock Networks (Part 2 of 2)

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{XZ}	2.754	5.406	2.754	5.848	2.754	6.412	2.754	7.159	ns
t_{ZX}	2.754	5.406	2.754	5.848	2.754	6.412	2.754	7.159	ns
$t_{INSUPLL}$	1.265		1.236		1.403		1.756		ns
t_{INHPLL}	0.000		0.000		0.000		0.000		ns
$t_{OUTCOPLL}$	1.068	2.302	1.068	2.483	1.068	2.510	1.068	2.423	ns
t_{XZPLL}	1.008	2.176	1.008	2.351	1.008	2.386	1.008	2.308	ns
t_{ZXPLL}	1.008	2.176	1.008	2.351	1.008	2.386	1.008	2.308	ns

Table 4–76. EP1S30 External I/O Timing on Row Pins Using Fast Regional Clock Networks

Parameters	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.616		2.808		3.223		3.797		ns
t_{INH}	0.000		0.000		0.000		0.000		ns
t_{OUTCO}	2.542	5.114	2.542	5.502	2.542	5.965	2.542	6.581	ns
t_{XZ}	2.569	5.168	2.569	5.558	2.569	6.033	2.569	6.663	ns
t_{ZX}	2.569	5.168	2.569	5.558	2.569	6.033	2.569	6.663	ns

Table 4–95. EP1S80 External I/O Timing on Row Pins Using Regional Clock Networks Note (1)

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.295		2.454		2.767		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.917	5.732	2.917	6.148	2.917	6.705	NA	NA	ns
t_{XZ}	2.944	5.786	2.944	6.204	2.944	6.773	NA	NA	ns
t_{ZX}	2.944	5.786	2.944	6.204	2.944	6.773	NA	NA	ns
$t_{INSUPLL}$	1.011		1.161		1.372		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
$t_{OUTCOPLL}$	1.808	3.169	1.808	3.209	1.808	3.233	NA	NA	ns
t_{XZPLL}	1.835	3.223	1.835	3.265	1.835	3.301	NA	NA	ns
t_{ZXPLL}	1.835	3.223	1.835	3.265	1.835	3.301	NA	NA	ns

Table 4–96. EP1S80 External I/O Timing on Rows Using Pin Global Clock Networks Note (1)

Symbol	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.362		1.451		1.613		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	3.457	6.665	3.457	7.151	3.457	7.859	NA	NA	ns
t_{XZ}	3.484	6.719	3.484	7.207	3.484	7.927	NA	NA	ns
t_{ZX}	3.484	6.719	3.484	7.207	3.484	7.927	NA	NA	ns
$t_{INSUPLL}$	o.994		1.143		1.351		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
$t_{OUTCOPLL}$	1.821	3.186	1.821	3.227	1.821	3.254	NA	NA	ns
t_{XZPLL}	1.848	3.240	1.848	3.283	1.848	3.322	NA	NA	ns
t_{ZXPLL}	1.848	3.240	1.848	3.283	1.848	3.322	NA	NA	ns

Note to Tables 4–91 to 4–96:
(1) Only EP1S25, EP1S30, and EP1S40 devices have the -8 speed grade.

Table 4–126. High-Speed I/O Specifications for Wire-Bond Packages (Part 2 of 2)

Symbol	Conditions	-6 Speed Grade			-7 Speed Grade			-8 Speed Grade			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
SW	PCML (J = 4, 7, 8, 10) only	800			800			800			ps
	PCML (J = 2) only	1,200			1,200			1,200			ps
	PCML (J = 1) only	1,700			1,700			1,700			ps
	LVDS and LVPECL (J = 1) only	550			550			550			ps
	LVDS, LVPECL, HyperTransport technology (J = 2 through 10) only	500			500			500			ps
Input jitter tolerance (peak-to-peak)	All			250			250			250	ps
Output jitter (peak-to-peak)	All			200			200			200	ps
Output t_{RISE}	LVDS	80	110	120	80	110	120	80	110	120	ps
	HyperTransport technology	120	170	200	120	170	200	120	170	200	ps
	LVPECL	100	135	150	100	135	150	100	135	150	ps
	PCML	80	110	135	80	110	135	80	110	135	ps
Output t_{FALL}	LVDS	80	110	120	80	110	120	80	110	120	ps
	HyperTransport	110	170	200	110	170	200	110	170	200	ps
	LVPECL	100	135	160	100	135	160	100	135	160	ps
	PCML	110	145	175	110	145	175	110	145	175	ps
t_{DUTY}	LVDS (J = 2 through10) only	47.5	50	52.5	47.5	50	52.5	47.5	50	52.5	%
	LVDS (J =1) and LVPECL, PCML, HyperTransport technology	45	50	55	45	50	55	45	50	55	%
t_{LOCK}	All			100			100			100	µs

Table 4–129. Enhanced PLL Specifications for -7 Speed Grade (Part 2 of 2)

Symbol	Parameter	Min	Typ	Max	Unit
$t_{OUTDUTY}$	Duty cycle for external clock output (when set to 50%)	45		55	%
t_{JITTER}	Period jitter for external clock output *(6)*			±100 ps for >200-MHz `outclk` ±20 mUI for <200-MHz `outclk`	ps or mUI
$t_{CONFIG5,6}$	Time required to reconfigure the scan chains for PLLs 5 and 6			$289/f_{SCANCLK}$	
$t_{CONFIG11,12}$	Time required to reconfigure the scan chains for PLLs 11 and 12			$193/f_{SCANCLK}$	
$t_{SCANCLK}$	`scanclk` frequency *(5)*			22	MHz
t_{DLOCK}	Time required to lock dynamically (after switchover or reconfiguring any non-post-scale counters/delays) *(7)* *(11)*	*(9)*		100	µs
t_{LOCK}	Time required to lock from end of device configuration *(11)*	10		400	µs
f_{VCO}	PLL internal VCO operating range	300		600 *(8)*	MHz
t_{LSKEW}	Clock skew between two external clock outputs driven by the same counter		±50		ps
t_{SKEW}	Clock skew between two external clock outputs driven by the different counters with the same settings		±75		ps
f_{SS}	Spread spectrum modulation frequency	30		150	kHz
% spread	Percentage spread for spread spectrum frequency *(10)*	0.5		0.6	%
t_{ARESET}	Minimum pulse width on `areset` signal	10			ns

Table 4–130. Enhanced PLL Specifications for -8 Speed Grade (Part 1 of 3)

Symbol	Parameter	Min	Typ	Max	Unit
f_{IN}	Input clock frequency	3 *(1)*, *(2)*		480	MHz
f_{INPFD}	Input frequency to PFD	3		420	MHz
f_{INDUTY}	Input clock duty cycle	40		60	%
$f_{EINDUTY}$	External feedback clock input duty cycle	40		60	%
$t_{INJITTER}$	Input clock period jitter			±200 *(3)*	ps

process and operating conditions. Run the timing analyzer in the Quartus II software at the fast and slow operating conditions to see the phase shift range that is achieved below these frequencies.

Table 4–135. Stratix DLL Low Frequency Limit for Full Phase Shift

Phase Shift	Minimum Frequency for Full Phase Shift	Unit
72°	119	MHz
90°	149	MHz

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